Abstracts

An empirical-table based FET model

I. Angelov, N. Rorsman, J. Stenarson, M. Garcia and H. Zirath. "An empirical-table based FET model." 1999 MTT-S International Microwave Symposium Digest 99.2 (1999 Vol. II [MWSYM]): 525-528 vol.2.

A new large signal field effect transistor (FET) model combining empirical and table based models was developed and investigated experimentally. The Chalmers empirical model was used as a spline function for the table based model. Combining models improves accuracy and simplifies and speeds extraction. The procedure can be applied for other types of devices.

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